

MOBILE MULTIMEDIA INTERFACE (M²I) VERY LOW POWER 1.8V 16K X 16 SYNCHRONOUS DUAL-PORT STATIC RAM

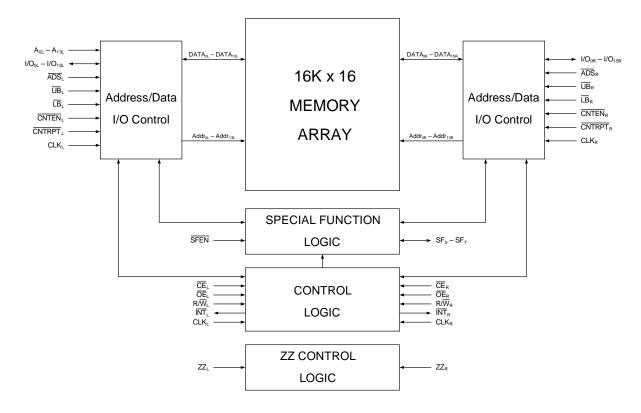
Datasheet IDT70P9268

Features

- True Dual-Ported Memory Cells
 - Allows simultaneous access of the same memory location
- High per-port throughput performance
 - Industrial: 800 Mbps
- **♦** Low-Power Operation
 - Active: 15 mA (typ.)
 - Standby: 2 uA (typ.)
- Multiplexed address and data I/Os

- Counter enable and repeat features
- Full synchronous operation on both ports
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- ◆ LVTTL-compatible, single 1.8V (+/- 100mV) power supply
- Industrial temperature range (-40C to +85C)
- Available in a 100-ball fpBGA (fine pitch BGA)
- ◆ Green parts available, see ordering information

Block Diagram



NOTES:

1. This block diagram depicts operation with the address and data signals mux'd on the right port but not on the left port. If each port is set to operate with the address and data signals mux'd, then both sides of the block diagram will be the same as the right port pictured above.

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Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM

Industrial Temperature Range

Device Description

Designed primarily for use as a high-speed, low-power inter-connect in multi-processor wireless handsets, the IDT70P9268 or Mobile Multimedia Interconnect (M²I) provides many advantages over embedded serial interfaces, asynchronous memories, and other legacy solutions to interprocessor communication.

Performance

The M²I supports unparalleled data throughput rates of up to 900 Mbps per port. This is achieved through the implementation of a synchronous architecture which allows the device to support much shorter cycle times (20 ns compared to 55 ns for most low-power asynchronous memories). Additionally, the adoption of a synchronous architecture allows the M²I to support on-chip counter functionality which helps to eliminate the inefficiencies associated with asynchronous implementations of the address-data-multiplex (ADM) interface. Asynchronous ADM (address-data multiplex) interfaces require the assertion of an external address on one cycle followed by the associated data on the subsequent cycle. This results in an access scheme that imparts a 50% inefficiency into a system already limited by slow cycle times. The M²I's counter functionality allows a single external address to be asserted on one cycle followed by data being burst into or out of the device on every subsequent cycle. This, when combined with the dramatically improved cycle time, translates to roughly six times greater throughput per-port when compared with asynchronous ADM devices.

Power Consumption

In portable applications, power consumption is of vital concern. This is why the M²I includes several features targeted at reducing the power consumption of the device itself and the system as a whole. First, the M²I was designed to consume 40% less operating current than low-power asynchronous memories (15 mA compared to 25 mA). When combined with it's superior performance and counter functionality, which allow it to complete media transfers in fewer cycles, this enables the M²I to consume nearly 90% less energy than asynchronous memories during transfers of a given file size. Second, the M²I features port-specific chip-enable and sleep mode pins which allow the two ports of the M²I to be powered down into standby mode independently of one another. When combined with the M²I's interrupt flag functionality, this allows the processor subsystems to communicate with one another and to shut off whole portions of the handset which are not in use, dramatically reducing the power consumption of the system.

Flexibility

To help meet the ever changing requirements of wireless handsets, the M²I has been designed to provide a great deal of flexibility. The M²I has the ability to support both ADM and traditional SRAM interfaces, allowing it to seamlessly interface with both current and legacy processors. Additionally, the M²I helps to free up GPIO pins on the processors, allowing designers to include differentiating functionality that helps set their product apart from the competition. By supporting the ADM interface, the M²I consumes nearly 50% fewer pins per-port than non-multiplexed solutions. The M²I also frees up additional GPIO pins on the processors by including 8 dynamically programmable GPIO extender pins. These pins allow the processors to offload the need to monitor or control simple, binary state devices (e.g. switches, LED drivers, etc.) to the M²I and allow the processors to use their GPIO pins for more value added functions.

Pin Configuration

IDT70P9268 BY100 100-BALL fpBGA

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10
Vss	I/O0R	VDD	I/O4R	I/O7R	VDD	I/O10R	VDD	I/O15R	SFEN
B1	B2	В3	B4	B5	B6	B7	B8	В9	B10
R/W̄R	CLKR	I/O1R	Vss	I/O5R	Vss	I/O11R	Vss	I/O14R	ŌĒR
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10
ĀDSR	CNTENR	CNTRPTR	I/O2R	I/O6R	I/O8R	I/O12R	ZZR	SF7	Vss
D1	D2	D3	D4	D5	D6	D7	D8	D9	D10
CER	ĪNTR	ŪBR	ŪBR	I/O3R	I/O9R	I/O13R	SF6	SF5	SF4
E1	E2	E3	E4	E5	E6	E7	E8	E9	E10
ĬNT∟	Vss	VDD	ŪBL	CNTRPTL	SF0	MSEL ⁽²⁾	VDD	Vss	VDD
F1	F2	F3	F4	F5	F6	F7	F8	F9	F10
CEL	ΪΒL	CNTENL	CLKL	Vss	A13L ⁽³⁾	SF2	Vss	Vss	SF1
G1	G2	G3	G4	G5	G6	G7	G8	G9	G10
ĀDSL	A0L ⁽³⁾	A3L ⁽³⁾	VDD	I/O8L	I/O12L	A7L ⁽³⁾	ZZL	ŌĒL	SF3
H1	H2	НЗ	H4	H5	H6	H7	Н8	H9	H10
R/WL	A2L ⁽³⁾	I/O0L	Vss	I/O4L	I/O11L	I/O13L	A9L ⁽³⁾	A12L ⁽³⁾	NC
J1	J2	J3	J4	J5	J6	J7	J8	J9	J10
A1L ⁽³⁾	A5L ⁽³⁾	I/O1L	I/O6L	I/O7L	I/O9L	VDD	I/O15L	A10L ⁽³⁾	A11L ⁽³⁾
K1	K2	K3	K4	K5	K6	K7	K8	K9	K10
A4L ⁽³⁾	A6L ⁽³⁾	I/O2L	I/O3L	I/O5L	VDD	I/O10L	Vss	I/O14L	A8L ⁽³⁾

The device setup shown above features multiplexed address and data signals on the right port and non-multiplexed address and data signals on the left port.
 For multiplexed address and data signal operation on the left port, this pin should be set to VDD. For non-multiplexed address and data signal operation on the left port, this pin should be set to VSS.
 For multiplexed address and data signal operation on the left port, these pins should be set to VSS.

Left Port	Right Port	Names
ΣĒ∟	\overline{CE}_R	Chip Enable (Input)
R/\overline{W}_L	R/\overline{W}_R	Read/Write Enable (Input)
ŌĒL	\overline{OE}_R	Output Enable (Input)
$A_{0L} - A_{15L}$	N/A	Address (Input)
$I/O_{0L} - I/O_{15L}$	N/A	Data (Input/Output)
N/A	$I/O + A_{0R} - I/O + A_{15R}$	Multiplexed Address and Data (Input/Output)
CLKL	CLK _R	Clock (Input)
$\overline{\sf UB}_{\sf L}$	$\overline{\sf UB}_{\sf R}$	Upper Byte Enable (Input)
\overline{LB}_L	\overline{LB}_R	Lower Byte Enable (Input)
ĀDSL	ĀŪS _R	Address Strobe Enable (Input)
CNTENL	ŪNTĒN _R	Counter Enable (Input)
CNTRPT _L	CNTRPT _R	Counter Repeat (Input)
ĪNŢ∟	ĪNT̄ _R	Interrupt Flag (Output)
ZZ_L	ZZ_R	Sleep Mode Enable (Input)
	SFEN	Special Function Enable (Input)
	SF ₀₋₇	Special Function I/O (Input/Output)
	MSEL	Left Port Mode Select (Input)
	V_{DD}	Power (1.8V)
	V _{SS}	Ground (0V)

Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Industrial Truth Table I - Read/Write and Enable Control (Multiplexed Port)

ŌĒ	CLK	ΖĒ	ŪΒ	ĪΒ	R/W	ADS	ZZ	Upper Byte	Lower Byte	Cycle	Address	Mode	
Х	↑	Η	Х	Χ	Χ	Χ	L	High Z	High Z	Х	Х	Deselected	
Х	↑	L	Н	Н	Х	Х	L	High Z	High Z	Х	Х	Both bytes deselected	
Х	↑	L	L	Н	L	L	L			N	A _N	Write to Upper Byte	
Х	1	Х	Х	Х	L	Н	L	D _{IN}	High Z	N+1		write to opper byte	
Х	↑	L	Н	L	L	L	L			N	A _N	Write to Lower Pute	
Х	↑	Χ	Х	Χ	L	Н	L	High Z	D _{IN}	N+1		Write to Lower Byte	
Х	1	L	L	L	L	L	L			N	A _N	Write to Both Butes	
Х	1	Χ	Х	Х	L	Н	L	D _{IN}	D _{IN}	N+1		Write to Both Bytes	
Н	↑	L	L	Н	Н	L	L			N	A_N	Pood Upper Pute Only	
L	↑	Χ	Х	Χ	Н	Н	L	D _{OUT}	High Z	N+2		Read Upper Byte Only	
Н	1	L	Н	L	Н	L	L			N	A _N	Read Lower Byte Only	
L	↑	Χ	Х	Χ	Н	Н	L	High Z	D _{OUT}	N+2		Read Lower Byte Only	
Н	↑	L	L	L	Н	L	L			N	A _N	Pood Roth Rytos	
L	1	Χ	Х	Х	Н	Н	L	D _{OUT}	D _{OUT}	N+2		Read Both Bytes	
Н	↑	L	L	L	Х	Н	L	High Z	High Z	Х	Х	Outputs Disabled	
Χ	Х	Χ	Х	Χ	Х	Х	Н	High Z	High Z	Х	Х	Sleep Mode – Power down	

Truth Table II - Read/Write and Enable Control (Non-Multiplexed Port)

ŌĒ	CLK	ΖĒ	ŪB	ĪΒ	R/W	ZZ	Upper Byte I/O	Lower Byte I/O	Mode
X	1	Н	Χ	Х	Х	L	High Z	High Z	Deselected
X	1	L	Η	Н	Χ	L	High Z	High Z	Both Bytes Deselected
X	1	L	L	Н	L	L	D _{IN}	High Z	Write To Upper Byte Only
Х	1	L	Η	L	L	L	High Z	D _{IN}	Write to Lower Byte Only
X	1	L	Ш	L	L	L	D _{IN}	D _{IN}	Write to Both Bytes
L	1	L	لــ	Η	Τ	L	D _{OUT}	High Z	Read Upper Byte Only
L	1	L	Η	L	Н	L	High Z	D _{OUT}	Read Lower Byte Only
L	1	L	L	L	Н	L	D _{OUT}	D _{OUT}	Read Both Bytes
Н	1	L	L	L	Х	L	High Z	High Z	Outputs Disabled
X	Х	Χ	Χ	Χ	X	Н	High Z	High Z	Sleep Mode – Power Down

Truth Table III - Address Counter Control

External Address	Previous Internal Address	Internal Address Used	CLK	ĀDS	CNTEN	CNTRPT	Mode
An	X	An	1	L	Х	Н	External Address Used
Х	An	A _{n+1}	1	Н	L	Н	Counter Enabled – Internal Address Generation
Х	A _{n + 1}	A _{n+1}	1	Н	Н	Н	External Address Blocked – Counter Disabled (A _{n+1} reused)
Х	Х	An	1	Х	Х	L	Counter Reset to Last External Address Loaded

Recommended Operating Temperature and Supply Voltage

Grade	Ambient Temperature	GND	VDD	
Industrial	-40°C to +85°C	0V	1.8V +/- 100mV	

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
VDD	Supply Voltage	1.7	1.8	1.9	V
Vss	Ground	0	0	0	V
ViH	Input High Voltage	1.2		VDD + 0.2	V
VIL	Input Low Voltage	-0.2		0.4	V

Absolute Maximum Ratings

Symbol	Rating	Industrial	Unit
V _{DD}	Voltage on Input, Output and I/O Terminals with Respect to Vss	-0.5V to V _{DD} +0.3V	V
VTERM	Terminal Voltage with Respect to GND	-0.5V to +2.9V	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Тѕтс	Storage Temperature	-65 to +150	°C
TJN	Junction Temperature	+150	°C
Іоит	DC Output Current	20	mA

Capacitance

Symbol	Parameter	Conditions	Max.	Unit
Cin	Input Capacitance	VIN = 0V	9	PF
Соит	Output Capacitance	VOUT = 0V	11	PF

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 1.8V + /- 100mV)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current	VIN = Vss to VDD		1	иA
ILO	Output Leakage Current	$\overline{CE}x = V_{IH} \text{ or } \overline{OE}x = V_{IH} \text{ or }$		1	иA
		Vout = Vss to VDD			
Vol	Output Low Voltage	IoL = 0.1mA, $VDD = Min$		0.2	V
Vон	Output High Voltage	IOH = -0.1 mA, VDD = Min	V _{DD} – 0.2V	-	V
Volsf	Output Low Voltage	IoL = 4mA, VDD = Min		0.4	V

Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Industrial Temperature Range DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 1.8V +/- 100mV)

Symbol	Parameter	Test Conditions	70P	9268
			Тур.	Max.
ldd	Dynamic Operating Current (Both Ports Active)	CEL and CER = VIL, Outputs Disabled, $f = f_{MAX}^{(1)}$	15 mA	25 mA
ISB1	Standby Current (Both Ports – TTL Inputs)	$\overline{CE}_L = \overline{CE}_R = V_{IH},$ Outputs Disabled, $f = f_{MAX}^{(1)}$	2 mA	4 mA
I _{SB2}	Standby Current (One Port – TTL Inputs)	\overline{CE} "A" = V _{IL} and \overline{CE} "B" = V _{IH} ⁽³⁾ , Active Port Outputs Disabled, $f = f_{MAX}^{(1)}$	3 mA	5 mA
IsB3	Full Standby Current (Both Ports CMOS Inputs)	Both Ports Outputs Disabled \overline{CE}_L and $\overline{CE}_R \ge V_{DD} - 0.2V$, $V_{IN} \ge V_{DD} - 0.2V$, or $V_{IN} \le 0.2V$, $f = 0^{(2)}$	2 <i>u</i> A	8 <i>u</i> A
I _{SB4}	Full Standby Current (One Port – CMOS Inputs)	$\overline{\text{CE}}$ "a" $\leq 0.2 \text{V}$ and $\overline{\text{CE}}$ "b" $\geq \text{V}_{DD} - 0.2 \text{V}$, $\text{V}_{IN} \geq \text{V}_{DD} - 0.2 \text{V}$ or $\text{V}_{IN} \leq 0.2 \text{V}$, Active Port Outputs Disabled, f = fmax ⁽¹⁾	3 mA	5 mA
lzz	Sleep Mode Current	ZZL and $ZZR > VDD - 0.2V$	2 <i>u</i> A	8 <i>u</i> A

NOTES:

- 1. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 1.8V.
- 2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.
- 3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

AC Test Conditions

Input Pulse Levels	Vss to Vdd
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	VDD/2
Output Reference Levels	VDD/2
Output Load	Figure 1

1.	8V
R1	13500Ω
R2	13500Ω

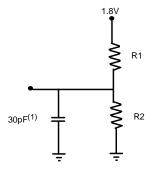


Figure 1. AC Output Test Level (5pF for tLz, tHz, twz, tow)

IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Industrial Temperature AC Electrical Characteristics Over the Operating Temperature Range

(Read and Write Cycle Timing for Multiplexed Port) (VDD = 1.8V +/- 100mV)

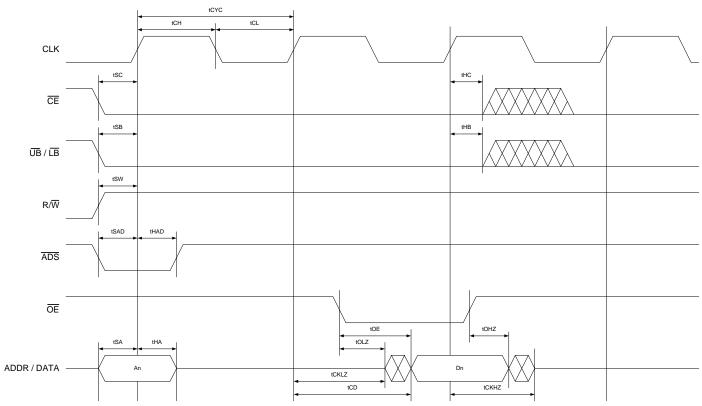
		70P9 Ind.		
Symbol	Parameter	Min.	Max.	Unit
t _{CYC}	Clock Cycle Time	20		ns
t _{CH}	Clock High Time	8		ns
t _{CL}	Clock Low Time	8		ns
t _R	Clock Rise Time		3	ns
t _F	Clock Fall Time		3	ns
t _{SA}	Address Setup Time	5		ns
t _{HA}	Address Hold Time	1		ns
t _{SB}	Bite Enable Setup Time	5		ns
t _{HB}	Bite Enable Hold Time	1		ns
t _{SC}	Chip Enable Setup Time	5		ns
t _{HC}	Chip Enable Hold Time	1		ns
t _{SW}	R/W Setup Time	5		ns
t _{HW}	R/W Hold Time	1		ns
t _{SD}	Input Data Setup Time	5		ns
t _{HD}	Input Data Hold Time	1		ns
t _{SAD}	ADS Setup Time	5		ns
t _{HAD}	ADS Hold Time	1		ns
t _{SCN}	CNTEN Setup Time	5		ns
t _{HCN}	CNTEN Hold Time	1		ns
t _{SRST}	CNTRST Setup Time	5		ns
t _{HRST}	CNTRST Hold Time	1		ns
toE	Output Enable to Data Valid		10	ns
t _{OLZ}	Output Enable to Low Z	2		ns
t _{OHZ}	Output Enable to High Z		10	ns
t _{CD}	Clock to Data Valid		12	ns
t _{DC}	Data Output Hold After Clock High	2		ns
t _{CKHZ}	Clock High to Output High Z	2	9	ns
t _{CKLZ}	Clock High to Output Low Z	2		ns
t _{INS}	Interrupt Flag Set Time	12		ns
t _{INR}	Interrupt Flag Reset Time	12		ns
t _{co}	Clock to Clock Offset	5		ns

IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Industrial Temperature AC Electrical Characteristics Over the Operating Temperature Range

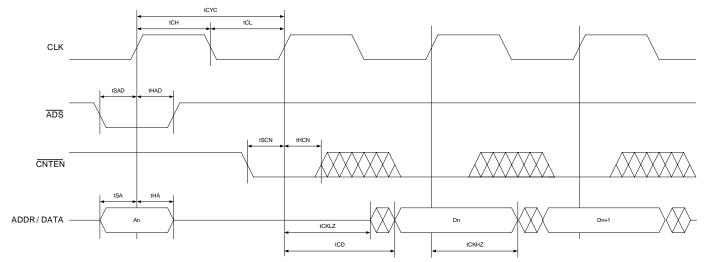
(Read and Write Cycle Timing for Non-Multiplexed Port) (VDD = 1.8V +/- 100mV)

		70P9 Ind.			
Symbol	Parameter	Min.	Max.	Unit	
t _{CYC}	Clock Cycle Time	20		ns	
t _{CH}	Clock High Time	8		ns	
t _{CL}	Clock Low Time	8		ns	
t _R	Clock Rise Time		3	ns	
t _F	Clock Fall Time		3	ns	
t _{SA}	Address Setup Time	5		ns	
t _{HA}	Address Hold Time	1		ns	
t _{SB}	Bite Enable Setup Time	5		ns	
t _{HB}	Bite Enable Hold Time	1		ns	
t _{SC}	Chip Enable Setup Time	5		ns	
t _{HC}	Chip Enable Hold Time	1		ns	
t _{SW}	R/W Setup Time	5		ns	
t _{HW}	R/W Hold Time	1		ns	
t _{SD}	Input Data Setup Time	5		ns	
t _{HD}	Input Data Hold Time	1		ns	
t _{SAD}	ADS Setup Time	5		ns	
t _{HAD}	ADS Hold Time	1		ns	
t _{SCN}	CNTEN Setup Time	5		ns	
t _{HCN}	CNTEN Hold Time	1		ns	
t _{SRST}	CNTRST Setup Time	5		ns	
t _{HRST}	CNTRST Hold Time	1		ns	
toE	Output Enable to Data Valid		10	ns	
t _{OLZ}	Output Enable to Low Z	2		ns	
t _{OHZ}	Output Enable to High Z		10	ns	
t _{CD}	Clock to Data Valid		12	ns	
t _{DC}	Data Output Hold After Clock High	2		ns	
t _{CKHZ}	Clock High to Output High Z	2	10	ns	
t _{CKLZ}	Clock High to Output Low Z	2		ns	
t _{INS}	Interrupt Flag Set Time	12		ns	
t _{INR}	Interrupt Flag Reset Time	12		ns	
t _{co}	Clock to Clock Offset	5		ns	

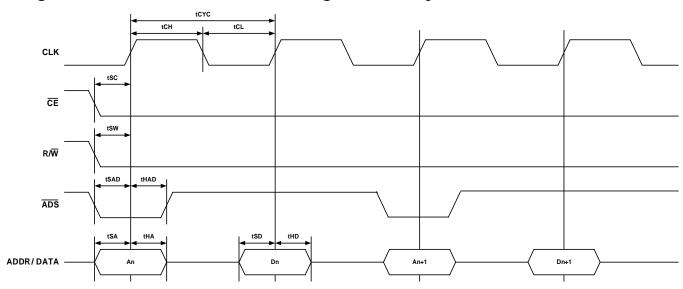
IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Timing Waveform for Mux'd Port Single Read Cycle



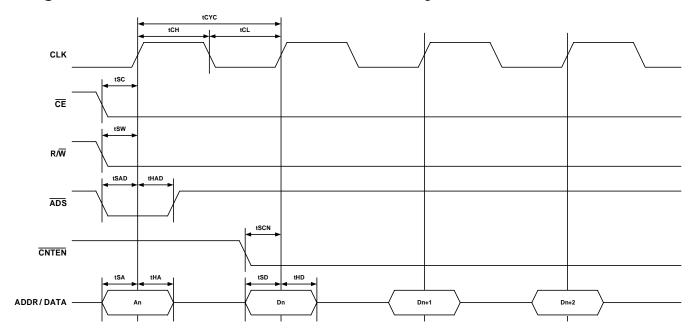
Timing Waveform for Mux'd Port Burst Read Cycle



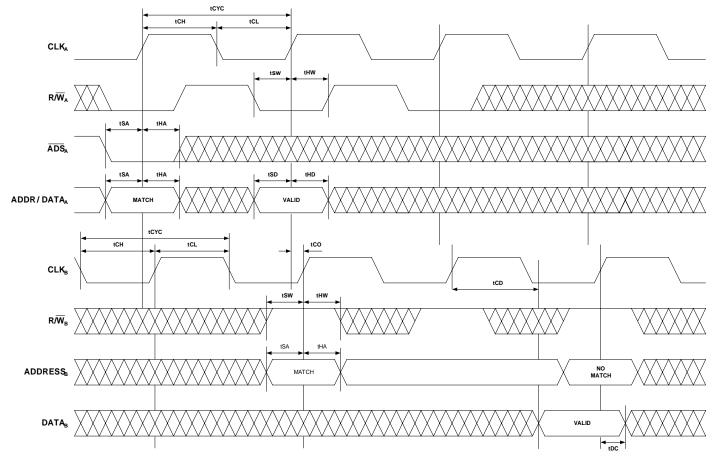
IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Timing Waveform for Mux'd Port Single Write Cycle



Timing Waveform for Mux'd Port Burst Write Cycle



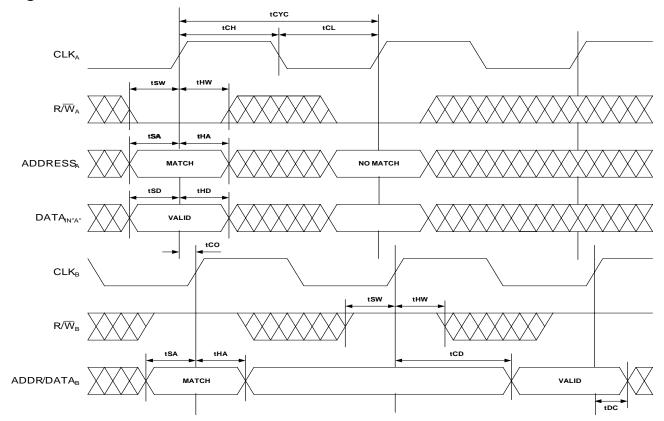
IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Indus Timing Waveform of Mux'd Port Write to Non-Mux'd Port Read



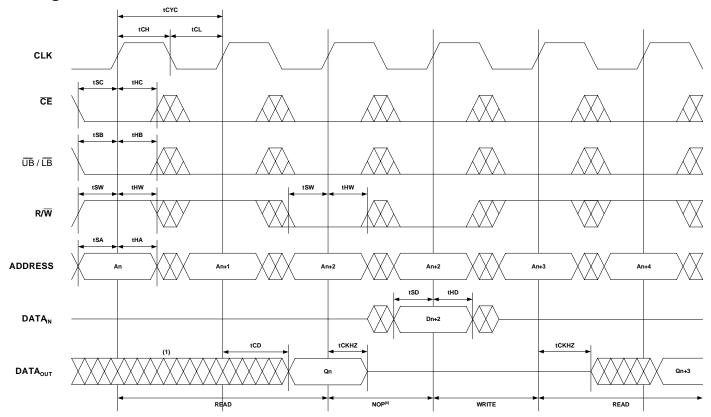
NOTES:

^{1.} CE, UB/LBn = VIL; CNTEN and CNTRPT = VIH.
2. OE = VIL for Port, which is being read from. OE = VIH for Mux'd Port, which is being written to.
3. If tco ≤ minimum specified, then data from Non-Mux'd Port read is not valid until following Non-Mux'd Port clock cycle (i.e., time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from Non-Mux'd Port read is available on first Non-Mux'd Port clock cycle (i.e., time from write to valid read on opposite port will be tco + tcyc2 + tcp2).

IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Indus Timing Waveform of Non-Mux'd Port Write to Mux'd Port Read



IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Timing Waveform of Non-Mux'd Port Read-to-Write-to-Read

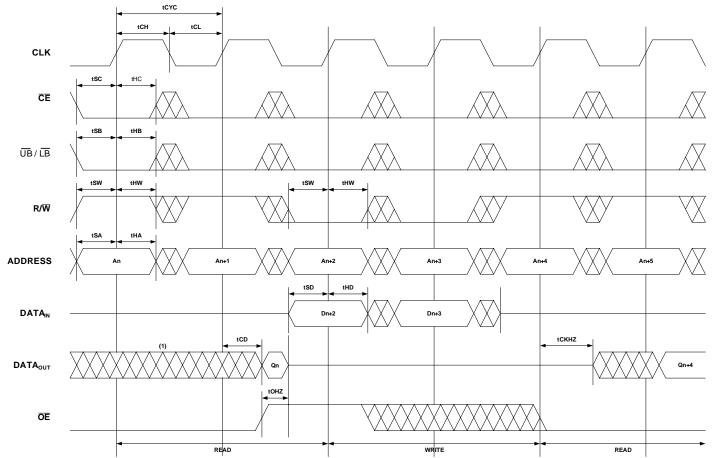


NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals. 2. $\overline{\text{CE}}$ and $\overline{\text{ADS}} = \text{VIL}$; $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRPT}} = \text{VIH}$. "NOP" is "No Operation".
- 3. Addresses do not have to be accessed sequentially since \overline{ADS} = ViL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only.

 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

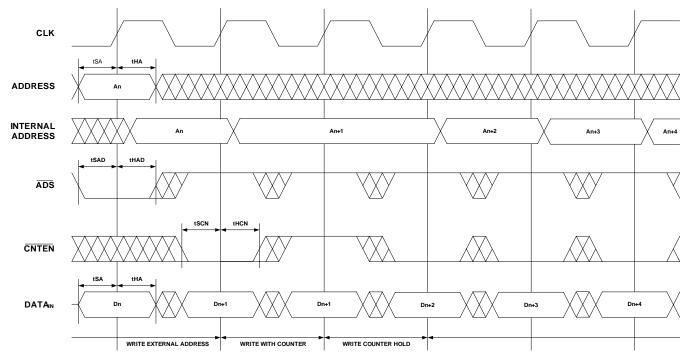
IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Industrial Temperature Range Timing Waveform of Non-Mux'd Port Read-to-Write-to-Read (OE Controlled)



NOTES:

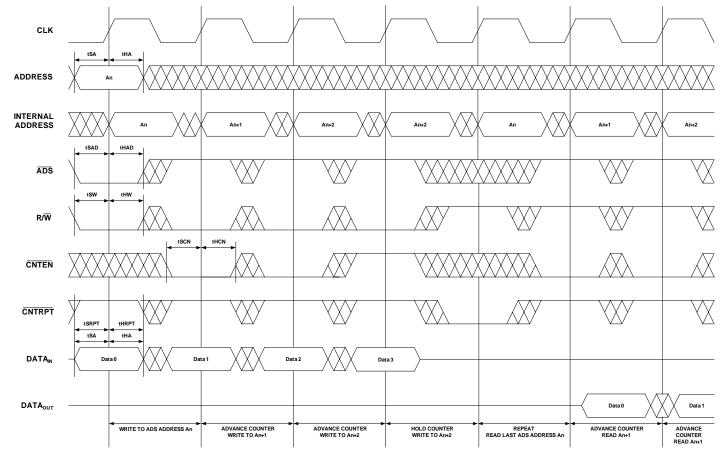
- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals. 2. $\overline{\text{CE}}$ and $\overline{\text{ADS}}$ = V_{IL}; $\overline{\text{CNTEN}}$, and $\overline{\text{CNTRPT}}$ = V_{IH}. "NOP" is "NO Operation".
- 3. Addresses do not have to be accessed sequentially since \overline{ADS} = Vil. constantly loads the address on the rising edge of the CLK; numbers are for reference use only.

IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Industrial Temperature Range Timing Waveform of Non-Mux'd Port Write with Counter Advance



NOTES:
1. <u>CE</u>, <u>UB/LB</u>, and R/W = V_{IL}; <u>CNTRPT</u> = V_{IH}.
2. <u>CE</u>, <u>UB/LB</u> = V_{IL}.
3. <u>The "Int</u>ernal Address" is equal to the "External Address" when <u>ADS</u> = V_{IL} and equals the counter output when <u>ADS</u> = V_{IH}.
4. <u>CNTEN</u> = V_{IL} advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this

Timing Waveform of Non-Mux'd Port Operation with Counter Repeat



NOTES:

1. \overline{CE} , $\overline{UB}/\overline{LB}$ = VIL.

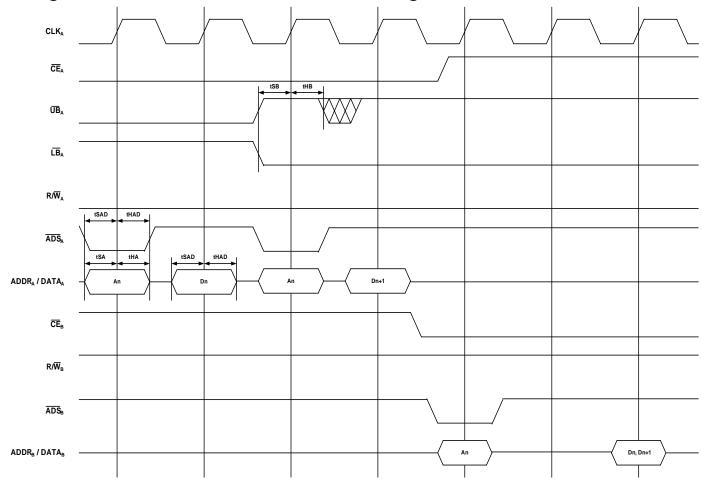
3. No dead cycle exists during CNTRPT operation. A READ or WRITE cycle may be coincidental with the counter CNTRPT cycle: Address loaded by last valid ADS load will be accessed.

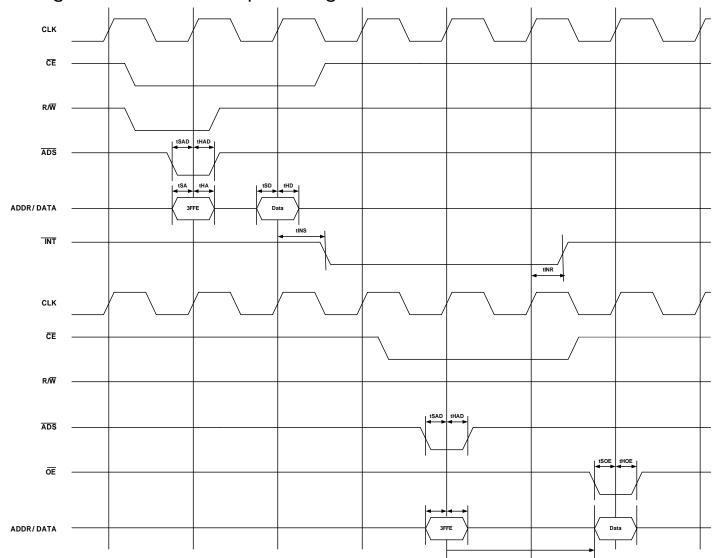
4. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this

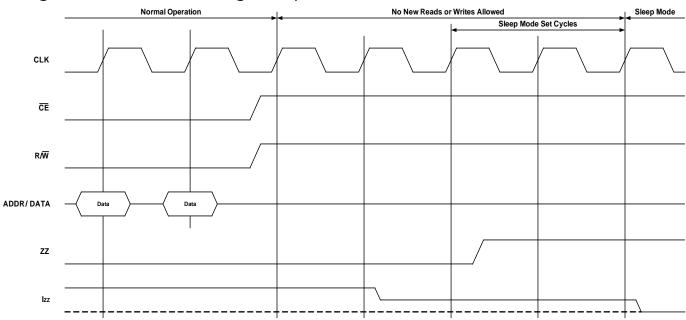
^{2.} The "Internal Address" is equal to the "External Address" when $\overline{ADS} = VIL$ and equals the counter output when $\overline{ADS} = VIH$.

cycle.

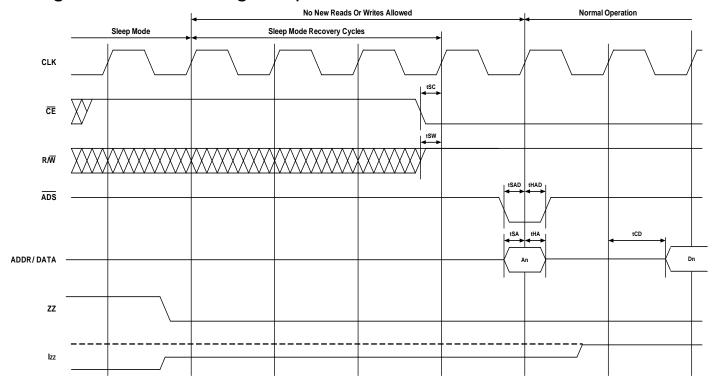
IDT70P9268 Very Low Power 16K x 16 Synchronous Mobile Multimedia Interface (M²I) Dual Port Static RAM Timing Waveform for x8 to x16 Bus Matching







Timing Waveform - Exiting Sleep Mode



Functional Description

The 70P9268L provides a true synchronous multiplexed and non-multiplexed Dual-Port Static RAM interface. Registered inputs provide minimal setup and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal. Counter enable and counter repeat inputs are provided to facilitate burst reads and writes to the memory.

Synchronous Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ($\overline{\text{INTL}}$) is asserted when the right port writes to memory location 3FFE (HEX), where a write is defined as $\overline{\text{CE}}_R = R/\overline{W}_R = \text{VIL}$. The left port clears the interrupt through access of address location 3FFE when $\overline{\text{CE}}_L = \text{VIL}$, $R/\overline{W}_L = \text{VIH}$. Likewise, the right port interrupt flag ($\overline{\text{INTR}}$) is asserted when the left port writes to memory location 3FFF (HEX) and to clear the interrupt flag ($\overline{\text{INTR}}$), the right port must read the memory location 3FFF. The message (16 bits) at 3FFE or 3FFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address, locations 3FFE and 3FFF are not used as mail boxes, but as part of the random access memory.

Truth Table IV - Interrupt Flag

Left Port					Right Port					
CLKL	R/W̄∟	ĒΕ∟	ADD_L	ĪNŦ∟	CLK _R	R/\overline{W}_R	C E _R	ADD_R	ĪÑ₹ĸ	Function
1	L	L	3FFF	Χ	1	X	Х	Х	L	Set Right INTR Flag
1	Х	Х	X	Χ	^	Н	L	3FFF	Н	Reset Right INTR Flag
1	Х	Х	X	L	1	L	L	3FFE	Χ	Set Left INTL Flag
1	Н	L	3FFE	Н	1	X	Х	X	X	Reset Left INTL Flag

Advanced Input Read and Output Drive Registers

The IDT70P9268L is equipped with 8 Special Function (SFx) pins that can be programmed to function as either Input Read Register (IRR) or Output Drive Register (ODR) pins. IRR pins allow the user to capture the status of external binary state devices and report that status to a processor, ASIC, FPGA, etc. via a standard read access from either port. ODR pins allow the user to monitor and control the state of external binary state devices via standard reads and writes from either port. The functionality of the SF pins are determined by the status of the Pin Direction Register (PDR). Refer to Truth Table V for information on programming the PDR and operating the special function pins.

Truth Table V - Input Read and Output Drive Registers

SFEN	ADDR	R/₩	1/00 – 1/07	1/08	I/O9 – I/O15	Function
L	0	L	Note 1	Н	X	Program Pin Direction Register
L	0	Н	Note 2	Note 3	Note 3	Reading the status of SFn and PDRn
L	0	L	Note 4	L	Χ	Write to Output Drive Register

NOTES:

- 1. If I/On = H, SFn is programmed as an output and I/On will be used to read and write to this ODR location during subsequent transactions when I/O8 = L. If I/On= L, SFn is programmed as an input and I/On will be used to read this IRR location during subsequent reads where I/O8 = L.
- 2. For n = 0-7. If PDRn = 0, I/On = IRRn (the registered value of SFn). If PDRn = 1, I/On = ODRn (the value last written to ODRn).
- 3. For n = 8-15, I/On = PDRn-8.
- 4. For I/Oo I/O7, the value written to I/On will be input to each ODRn location (where PDRn = 1) with a "1" corresponding to "on" and a "0" corresponding to "off".

Special Function I/O Operation

I/O	Function
0 – 7	With $\overline{SFEN} = L$, I/O8 = H, the value written to address 0 on I/On will determine the status of PDRn (1 = output, 0 = input). With $\overline{SFEN} = L$, I/O8 = L, the value written to address 0 on I/On will be input to the corresponding ODRn location (1 = on, 0 = off).
8	With $\overline{SFEN} = L$, writing a "0" to address 0 on this I/O causes the values of I/O ₀ – I/O ₇ to be input to their corresponding ODR locations. With $\overline{SFEN} = L$, writing a "1" to address 0 on this I/O causes the values of I/O ₀ – I/O ₇ to be input to their corresponding PDR locations, which in turn determine whether SF ₀ – SF ₇ are individually programmed to be inputs (IRR) or outputs (ODR).
9 – 15	With \overline{SFEN} = L, reads to address 0 will output the status of the PDR, where I/On = PDRn-8

The PDR determines whether the SFx pins will operate as IRR or ODR. The PDR is programmed by writing to address x0000 with $\overline{\text{SFEN}} = \text{VIL}$ and I/O8 = H. Writing a "0" to I/Ox will set SFx to be an IRR pin. Writing a "1" to I/Ox will set SFx to be an ODR pin.

The status of the Special Function pins and the PDR can be read as a standard memory access to address x0000 from either port and the data is output via the standard I/Os (Truth Table V). During Special Function reads I/O0 - I/O7 output the status of the Special Function pins with I/On corresponding to SFn. I/O8 - I/O15 outputs the status of the Pin Direction Register with I/On = PDRn-8.

For SF pins set to ODR operation, the status of these pins is determined by using standard write accesses from either port to address x0000 with SFEN = VIL and I/O8 = L. A written "1" will correspond to "on" for the connected binary state device and a written "0" will correspond to "off".

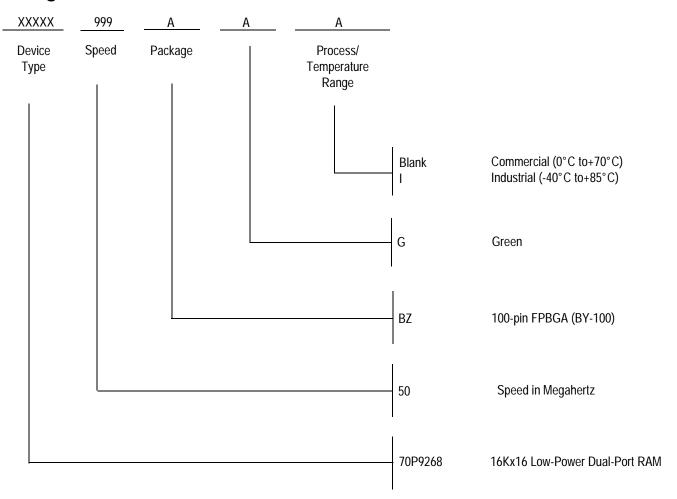
Sleep Mode

The IDT70P9268 is equipped with an optional sleep or low-power mode on both ports. The sleep mode pin on both ports is asynchronous and active high. During normal operation, the ZZ-pin is pulled low. When ZZ is pulled high, the port will enter sleep mode where it will meet lowest possible power conditions. The sleep mode timing diagram shows the modes of operation: Normal Operation, No Read/Write Allowed and Sleep Mode.

For normal operation all inputs must meet setup and hold times prior to sleep and after recovering from sleep. Clocks must also meet cycle high and low times during these periods. Three cycles prior to asserting ZZ (ZZX = VIH) and three cycles after de-asserting ZZ (ZZX = VIL), the device must be disabled via the chip enable pins. If a write or a read operation occurs during these periods, the memory array may be corrupted. Validity of data out from the RAM cannot be guaranteed immediately after ZZ is asserted (prior to being in sleep). When exiting sleep mode, the device must be in Read mode ($R/\overline{W}X = VIH$) when chip enable is asserted, and the chip enable must be valid for one full cycle before a read will result in the output of valid data.

During sleep mode the RAM automatically deselects itself. The RAM disconnects its internal clock buffer. The external clock may continue to run without impacting the RAMs sleep current (Izz). All outputs will remain in high-Z state while in sleep mode. All inputs are allowed to toggle. The RAM will not be selected and will not perform any reads or writes.

Ordering Information



Revision History

02/06/07: Initial Release

08/21/07: Final Datasheet. Initial Release

11/16/07: Signal corrections - added overbars to indicate low active signals. See pages 3, 4, 5, 21 & 22.

 $FBD\ correction\ -\ changed\ signal\ arrow\ indicator\ for\ Addr_{0L}\ -\ Addr_{13L}\ and\ added\ overbar\ to\ SFEN\ to\ indicate\ low\ active\ signal.\ See\ page\ 1.$

Footnote correction - removed CE1 and replaced REPEAT with CNTRPT. See pages 12, 14, 15 & 16.

Footnote correction - removed UB/LB. See pages 14 & 15.

Unit measurement column corrected for DC Electrical Chars Over Operating Temp & Supply Voltage Range table. See page 6.

Added Bite Enable Setup Time (tsb), Bite Enable Hold Time (thb) values and the unit measurement column to the AC Electrical Chars Over Operating Temp Range tables. See pages 8 & 9.

Added Output Enable to Data Valid (toe) values to the AC Electrical Chars Over Operating Temp Range table (non-multiplexed port). See page 9.

Corrected the Clock High to Output Low Z (tckLz) symbol in the Timing Waveform for Mux'd Port Single Read Cycle. See page 10.

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